

L Number	Hits	Search Text	DB	Time stamp
4	0	c23c016\$.ipc. and (etch\$3 with inlet with separat\$3)	JPO; DERWENT	2003/01/27 09:15
7	0	c23c016\$.ipc. and (oxygen with etch\$3 with inlet with separat\$3)	JPO; DERWENT	2003/01/27 09:21
10	0	(118/\$.ccls. 156/345\$.ccls.) and (oxygen with etch\$3 with inlet with separat\$3)	USPAT; US-PGPUB	2003/01/27 12:20
13	11	(118/\$.ccls. 156/345\$.ccls.) and (etch\$3 with inlet with separat\$3)	USPAT; US-PGPUB	2003/01/27 09:22
16	0	oxygen with etch\$3 with inlet with separat\$3	JPO; DERWENT	2003/01/27 09:18
19	11	etch\$3 with inlet with separat\$3	JPO; DERWENT	2003/01/27 09:18
22	0	c23c016\$.ipc. and (oxidiz\$3 with etch\$3 with inlet with separat\$3)	JPO; DERWENT	2003/01/27 09:21
25	0	oxidiz\$3 with etch\$3 with inlet with separat\$3	JPO; DERWENT	2003/01/27 09:21
28	61	(etch\$3 with inlet with separat\$3)	USPAT; US-PGPUB	2003/01/27 09:22
31	0	(oxidiz\$3 with etch\$3 with inlet with separat\$3)	USPAT; US-PGPUB	2003/01/27 09:22
34	50	((etch\$3 with inlet with separat\$3)) not ((118/\$.ccls. 156/345\$.ccls.) and (etch\$3 with inlet with separat\$3))	USPAT; US-PGPUB	2003/01/27 09:26
37	1841	(118/715).CCLS.	USPAT; US-PGPUB	2003/01/27 10:45
44	3462	silylation	USPAT; US-PGPUB	2003/01/27 10:48
47	399	silylation and etch\$3	USPAT; US-PGPUB	2003/01/27 10:45
50	53	silylation and etch\$3 and ash\$3	USPAT; US-PGPUB	2003/01/27 10:46
53	0	silylation same etch\$3 same ash\$3	USPAT; US-PGPUB	2003/01/27 10:46
56	189	(silylation silane "hmds") same etch\$3 same ash\$3	USPAT; US-PGPUB	2003/01/27 10:47
59	115	silylation same (chamber reactor apparatus)	USPAT; US-PGPUB	2003/01/27 10:49
62	34	(silylation same (chamber reactor apparatus)) and etch	USPAT; US-PGPUB	2003/01/27 10:49
65	54	(silylation same (chamber reactor apparatus)) and etch\$3	USPAT; US-PGPUB	2003/01/27 12:19
68	6	4768291.URPN.	USPAT	2003/01/27 10:59
69	3	("3236073" "3943904" "4592926").PN.	USPAT	2003/01/27 11:01
71	18	4808511.URPN.	USPAT	2003/01/27 11:07
72	8	6001739.URPN.	USPAT	2003/01/27 11:15
73	3	("4751170" "4808511" "5322764").PN.	USPAT	2003/01/27 11:16
74	40	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (resist and ((spin with on) (physical evaporation)))	USPAT; US-PGPUB	2003/01/27 12:25
77	18	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (resist same spin)	USPAT; US-PGPUB	2003/01/27 12:26
-	38983	c23c016\$.ipc.	JPO; DERWENT	2003/01/27 09:14
-	660865	h011021\$.ipc.	JPO; DERWENT	2002/05/07 13:21
-	1320	118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.	USPAT; US-PGPUB	2003/01/25 18:29
-	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 and silylat\$3)	USPAT; US-PGPUB	2003/01/26 13:35
-	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and silylat\$3	USPAT; US-PGPUB	2003/01/25 18:30
-	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (silylation silylating)	USPAT; US-PGPUB	2003/01/25 18:31
-	0	118/\$.ccls. and (ash\$3 and silylat\$3)	USPAT; US-PGPUB	2003/01/25 18:33

-	377	ash\$3 and silylat\$3	USPAT; US-PGPUB	2003/01/27 10:45
-	68	ashing and silylat\$3	USPAT; US-PGPUB	2003/01/25 18:40
-	377	ash\$3 and silylat\$3	USPAT; US-PGPUB	2003/01/25 18:40
-	1	ash\$3 and silylat\$3 and (chamber reactor apparatus)	EPO; JPO; DERWENT	2003/01/25 18:42
-	0	c23c016\$.ipc. and (ash\$3 and silylat\$3)	EPO; JPO; DERWENT	2003/01/25 18:57
-	156	ash\$3 and silylat\$3 and (chamber reactor apparatus)	USPAT; US-PGPUB	2003/01/25 18:43
-	108	ash\$3 and silylat\$3 and (chamber reactor apparatus) and (wafer substrate semiconductor)	USPAT; US-PGPUB	2003/01/25 18:43
-	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 and silyl\$)	USPAT; US-PGPUB	2003/01/25 18:56
-	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 and "hmds")	USPAT; US-PGPUB	2003/01/25 18:58
-	0	c23c016\$.ipc. and (ash\$3 and silyl\$)	EPO; JPO; DERWENT	2003/01/26 13:12
-	0	c23c016\$.ipc. and (ash\$3 and "hmds")	EPO; JPO; DERWENT	2003/01/25 18:57
-	5	118/\$.ccls. and (ash\$3 and "hmds")	USPAT; US-PGPUB	2003/01/25 18:58
-	7	156/345.\$.ccls. and (ash\$3 and "hmds")	USPAT; US-PGPUB	2003/01/25 19:01
-	8	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (etch\$3 and (silyl\$5 "hmds"))	USPAT; US-PGPUB	2003/01/25 19:03
-	122	ash\$3 and "hmds" and (chamber reactor apparatus)	USPAT; US-PGPUB	2003/01/26 13:07
-	3	ash\$3 same "hmds" same (chamber reactor apparatus)	USPAT; US-PGPUB	2003/01/26 13:08
-	0	c23c016\$.ipc. and (ash\$3 and silylation)	EPO; JPO; DERWENT	2003/01/26 13:12
-	14	c23c016\$.ipc. and (ash\$3 and (silane "hmds" \$3silazane siloxysilane))	EPO; JPO; DERWENT	2003/01/26 13:13
-	230	(ash\$3 and (silane "hmds" \$3silazane siloxysilane))	EPO; JPO; DERWENT	2003/01/26 13:13
-	2171	(ash\$3 and (silane "hmds" \$3silazane siloxysilane)) and (chamber apparatus reactor)	USPAT; US-PGPUB	2003/01/26 13:21
-	32	(ash\$3 and (silane "hmds" \$3silazane siloxysilane)) and (chamber apparatus reactor)	EPO; JPO; DERWENT	2003/01/26 13:13
-	24	(ash\$3 same (silane "hmds" \$3silazane siloxysilane)) same (chamber apparatus reactor)	USPAT; US-PGPUB	2003/01/26 13:22
-	87	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 and etch\$3)	USPAT; US-PGPUB	2003/01/26 13:35
-	73	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 same etch\$3\$3)	USPAT; US-PGPUB	2003/01/26 13:53
-	14	(118/\$.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (ash\$3 same ozone)	USPAT; US-PGPUB	2003/01/26 14:18
-	137	(156/345.33).CCLS.	USPAT; US-PGPUB	2003/01/26 14:39
-	33	c23c016\$.ipc. and (separate with gas with inlet)	JPO; DERWENT	2003/01/26 14:52
-	0	156/345.33.ccls. and (separate with inlet)	USPAT; US-PGPUB	2003/01/26 14:41
-	3	156/345.33.ccls. and ((multiple plural) with inlet)	USPAT; US-PGPUB	2003/01/26 14:41

-	40	(US-6492068-\$ or US-6475904-\$ or US-5948702-\$ or US-5688723-\$ or US-5595941-\$ or US-5322764-\$ or US-4886565-\$ or US-4810601-\$ or US-5215790-\$ or US-6264748-\$ or US-5965034-\$ or US-5863338-\$ or US-5501739-\$ or US-5348619-\$ or US-3733893-\$ or US-5285301-\$ or US-5796121-\$ or US-RE36006-\$ or US-6168726-\$ or US-4996077-\$ or US-5110394-\$ or US-5134965-\$ or US-5164034-\$ or US-5223001-\$ or US-5306380-\$ or US-5376212-\$).did. or (US-5413664-\$ or US-5474641-\$ or US-5628828-\$ or US-5695564-\$ or US-5700127-\$ or US-5820679-\$ or US-5981399-\$ or US-6036816-\$).did. or (US-20020197878-\$).did. or (JP-04184917-\$ or JP-04073953-\$).did. or (US-4400411-\$ or WO-200217374-\$ or DE-19847455-\$).did.	USPAT; US-PGPUB; JPO; DERWENT	2003/01/26 14:43
-	0	((US-6492068-\$ or US-6475904-\$ or US-5948702-\$ or US-5688723-\$ or US-5595941-\$ or US-5322764-\$ or US-4886565-\$ or US-4810601-\$ or US-5215790-\$ or US-6264748-\$ or US-5965034-\$ or US-5863338-\$ or US-5501739-\$ or US-5348619-\$ or US-3733893-\$ or US-5285301-\$ or US-5796121-\$ or US-RE36006-\$ or US-6168726-\$ or US-4996077-\$ or US-5110394-\$ or US-5134965-\$ or US-5164034-\$ or US-5223001-\$ or US-5306380-\$ or US-5376212-\$).did. or (US-5413664-\$ or US-5474641-\$ or US-5628828-\$ or US-5695564-\$ or US-5700127-\$ or US-5820679-\$ or US-5981399-\$ or US-6036816-\$).did. or (US-20020197878-\$).did. or (JP-04184917-\$ or JP-04073953-\$).did. or (US-4400411-\$ or WO-200217374-\$ or DE-19847455-\$).did.) and (etch\$3 with inlet) and (ash\$3 with inlet)	USPAT; US-PGPUB	2003/01/26 14:43
-	10	(etch\$3 with inlet) and (ash\$3 with inlet)	USPAT; US-PGPUB	2003/01/26 14:44
-	4	(etch\$3 with inlet) and (ash\$3 with inlet)	EPO; JPO; DERWENT	2003/01/26 14:46
-	134	((118/\$.ccls. 156/345\$.ccls.) and (differ\$3 with inlet with gas)	USPAT; US-PGPUB	2003/01/26 14:51
-	2	c23c016\$.ipc. and (differ\$3 with inlet with gas) and etch\$3	JPO; DERWENT	2003/01/26 14:52
-	9	(differ\$3 with inlet with gas) and etch\$3	EPO; JPO; DERWENT	2003/01/26 14:53
-	69	((118/\$.ccls. 156/345\$.ccls.) and (differ\$3 with inlet with gas) and etch\$3	USPAT; US-PGPUB	2003/01/26 15:07
-	1762	((multi\$3 plural\$3) with process) and ((differ\$3 separa\$3 multi\$3 plural\$3)with inlet with gas)	USPAT; US-PGPUB	2003/01/26 15:11
-	148	((multi\$3 plural\$3) with process) and ((differ\$3 separa\$3 multi\$3 plural\$3)with inlet with gas)	EPO; JPO; DERWENT	2003/01/26 15:12
-	506	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)	USPAT; US-PGPUB	2003/01/26 15:13
-	149	((multi\$3 plural\$3) with process\$3) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)	EPO; JPO; DERWENT	2003/01/26 15:13
-	202	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (wafer semiconductor substrate)	USPAT; US-PGPUB	2003/01/26 15:20
-	42	((multi\$3 plural\$3) with process\$3) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (wafer substrate semiconductor)	EPO; JPO; DERWENT	2003/01/26 15:21
-	171	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (contamin\$5)	USPAT; US-PGPUB	2003/01/26 15:26
-	5	((multi\$3 plural\$3) with process\$3) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (contamin\$5)	EPO; JPO; DERWENT	2003/01/26 15:25
-	1	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) same (contamin\$5) same (mix\$3)	USPAT; US-PGPUB	2003/01/26 15:28
-	3	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (contamin\$5) and (mix\$3)	EPO; JPO; DERWENT	2003/01/26 15:29

-	105	((multi\$3 plural\$3) with process\$2) same ((differ\$3 separa\$3 multi\$3 plural\$3) with inlet with gas)) and (contamin\$5) and (mix\$3)	USPAT; US-PGPUB	2003/01/26 15:53
-	2	(inlet supply\$3 port) with gas with separate with contamination	EPO; JPO; DERWENT	2003/01/26 15:58
-	1	("5344542").PN.	USPAT; US-PGPUB	2003/01/26 15:56
-	14	(inlet supply\$3 port) with gas with separate with contamination	USPAT; US-PGPUB	2003/01/26 16:01
-	608	(inlet supply\$3 port) with gas with separate with (introduc\$3)	USPAT; US-PGPUB	2003/01/26 16:01
-	255	(inlet supply\$3 port) with gas with separate with (introduc\$3)	EPO; JPO; DERWENT	2003/01/26 16:02
-	25	c23c016\$.ipc. and ((inlet supply\$3 port) with gas with separate with (introduc\$3))	EPO; JPO; DERWENT	2003/01/26 16:03
-	40	(118/\$.ccls. 156/345\$.ccls.) and ((inlet supply\$3 port) with gas with separate with (introduc\$3))	USPAT; US-PGPUB	2003/01/26 16:30
-	24	(118/\$.ccls. 156/345\$.ccls.) and ((inlet supply\$3 port) with gas with ((succession alternat\$4) with (introduc\$3)))	USPAT; US-PGPUB	2003/01/26 16:26
-	1105	"atomic layer deposition" "ald"	USPAT; US-PGPUB	2003/01/26 16:30
-	24	("atomic layer deposition" "ald") and (separate with gas with (inlet port supply\$3))	USPAT; US-PGPUB	2003/01/26 16:32
-	36	("atomic layer deposition" "ald") and (gas with (inlet port supply\$3))	EPO; JPO; DERWENT	2003/01/26 16:40
-	63	(gas with (supply\$3 port inlet) with prevent\$3 with particulate)	EPO; JPO; DERWENT	2003/01/26 16:41
-	1	(gas with (supply\$3 port inlet) with prevent\$3 with particulate with separate)	EPO; JPO; DERWENT	2003/01/26 16:41
-	5	(gas with (supply\$3 port inlet) with prevent\$3 with particulate with separat\$3)	EPO; JPO; DERWENT	2003/01/26 16:41
-	22	(gas with (supply\$3 port inlet) with prevent\$3 with particulate with separat\$3)	USPAT; US-PGPUB	2003/01/26 16:45
-	7	(gas with (supply\$3 port inlet) with particulate with separat\$3) and (118/\$.ccls. or 156/345\$.ccls.)	USPAT; US-PGPUB	2003/01/26 16:47
-	682	(gas with (supply\$3 port inlet) with separat\$3) and (118/\$.ccls. or 156/345\$.ccls.)	USPAT; US-PGPUB	2003/01/26 16:49
-	216	(gas with (supply\$3 port inlet) with separat\$3) and (c23c016\$.ipc.)	EPO; JPO; DERWENT	2003/01/26 16:50
-	0	(gas with (supply\$3 port inlet) with separat\$3) and (118/\$.ccls. or 156/345\$.ccls.) same (prevent\$3 with (mix\$3 contaminat\$3 particle particulate))	USPAT; US-PGPUB	2003/01/26 16:52
-	17	(gas with (supply\$3 port inlet) with separat\$3) and (c23c016\$.ipc.) and (prevent\$3 with (mix\$3 contaminat\$3 particle particulate))	EPO; JPO; DERWENT	2003/01/26 16:52
-	199	(gas with (supply\$3 port inlet) with separat\$3) and (118/\$.ccls. or 156/345\$.ccls.) and (prevent\$3 with (mix\$3 contaminat\$3 particle particulate))	USPAT; US-PGPUB	2003/01/26 17:02
-	141	(gas with (supply\$3 port inlet) with separat\$3) and (118/\$.ccls. or 156/345\$.ccls.) and (prevent\$3 with (mix\$3 contaminat\$3 particle particulate))	USPAT; US-PGPUB	2003/01/26 17:04
-	7	("3785853" "4058430" "4480585" "4986214" "5108779" "5281274" "5338362").PN.	USPAT	2003/01/26 17:09
-	2	5730802.URPN.	USPAT	2003/01/26 17:11
-	36	("4058430" "4282267" "4747367" "4761269" "4851095" "4935661" "5071670" "5278435" "5281274" "5291066" "5294286" "5300186" "5321713" "5330610" "5356673" "5374570" "5395791" "5443033" "5443647" "5458084" "5469806" "5483919" "5484664" "5496582" "5618395" "5641984" "5693139" "5707880" "5711811" "5730802" "5769950" "5855680" "5916365" "6200893" "6203613" "6270572").PN.	USPAT	2003/01/26 17:12
-	5	("3464797" "5091217" "5872065" "5902403" "6099647").PN.	USPAT	2003/01/26 17:42